74AUP1GU04

Low-power unbuffered inverter Rev. 5 — 29 June 2012

Product data sheet

1. **General description**

The 74AUP1GU04 provides the single unbuffered inverting gate.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - ♦ MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

Type number	Package							
	Temperature range	perature range Name Description						
74AUP1GU04GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1				
74AUP1GU04GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886				
74AUP1GU04GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891				
74AUP1GU04GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115				
74AUP1GU04GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202				
74AUP1GU04GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226				



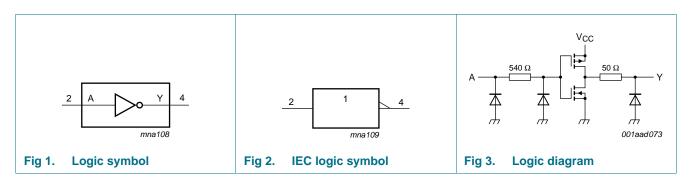
4. Marking

Table 2. Marking

Type number	Marking code[1]
74AUP1GU04GW	pD
74AUP1GU04GM	pD
74AUP1GU04GF	pD
74AUP1GU04GN	pD
74AUP1GU04GS	pD
74AUP1GU04GX	pD

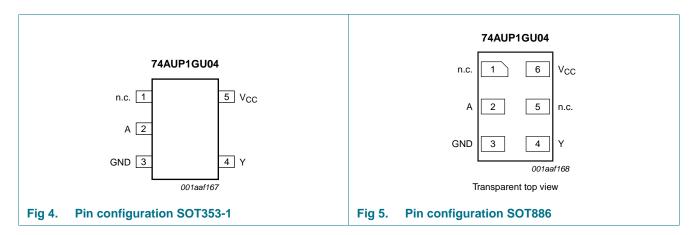
^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

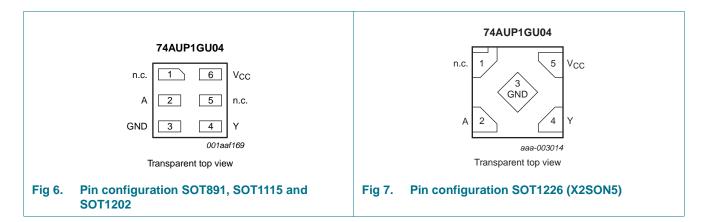
5. Functional diagram



6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
n.c.	1	1	not connected
Α	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table [1]

Input	Output
A	Υ
L	Н
H	L

^[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage		<u>[1]</u> –0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0 V$	-50	-	mA
V_{O}	output voltage		<u>[1]</u> –0.5	$V_{CC} + 0.5$	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±20	mA
I _{CC}	supply current		-	+50	mA
I_{GND}	ground current		–50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[2]</u> -	250	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
V_{I}	input voltage		0	3.6	V
Vo	output voltage		0	V_{CC}	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

^[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$T_{amb} = 2$	25 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	$0.25 \times V_{CC}$	٧
V _{OH}	HIGH-level output voltage	$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	$V_{CC}-0.1$	-	-	٧
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	٧
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	٧
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.5	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	1.5	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.8	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V to 3.6 V	$0.75 \times V_{CC}$	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V to 3.6 V	-	-	$0.25 \times V_{CC}$	V
V _{OH}	HIGH-level output voltage	$I_{O} = -20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	$V_{CC}-0.1$	-	-	V
		$I_O = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7 \times V_{CC}$	-	-	V
		$I_O = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_O = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_O = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_O = -2.7 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}$; $V_{CC} = 3.0 \text{ V}$	2.55	-	-	V

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OL}	LOW-level output voltage	I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I _I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
I _{CC}	supply current	$V_1 = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μΑ
T _{amb} = -	40 °C to +125 °C					
V_{IH}	HIGH-level input voltage	V _{CC} = 0.8 V to 3.6 V	$0.75 \times V_{CC}$	-	-	V
V_{IL}	LOW-level input voltage	V _{CC} = 0.8 V to 3.6 V	-	-	$0.25 \times V_{CC}$	V
V_{OH}	HIGH-level output voltage	$I_O = -20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	V _{CC} – 0.11	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V_{OL}	LOW-level output voltage	I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I _I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	ymbol Parameter Conditions			25 °C		-40 °C to +125 °C			Unit	
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F	1						1		
t _{pd}	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC} = 0.8 \text{ V}$		-	6.2	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		0.9	2.3	4.4	0.9	4.8	5.3	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		0.7	1.7	3.1	0.6	3.4	3.8	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		0.5	1.4	2.6	0.5	2.9	3.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.4	1.1	2.0	0.4	2.3	2.6	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.3	1.0	1.8	0.3	2.1	2.4	ns
C _L = 10	pF									
t _{pd}	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC} = 0.8 \text{ V}$		-	9.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		1.2	3.1	6.1	1.2	6.8	7.5	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.0	2.3	4.0	0.9	4.6	5.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		0.8	1.9	3.3	0.7	3.8	4.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.6	1.5	2.7	0.6	3.1	3.5	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.5	1.3	2.4	0.5	2.7	3.0	ns
C _L = 15	pF									
t _{pd}	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC} = 0.8 \text{ V}$		-	13.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		1.6	3.8	7.9	1.4	8.8	9.7	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.3	2.8	4.9	1.1	5.7	6.3	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	2.3	4.0	0.9	4.7	5.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.8	1.9	3.2	8.0	3.7	4.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.7	1.6	2.9	0.7	3.3	3.7	ns
C _L = 30	pF									
t _{pd}	propagation delay	A to Y; see Figure 8	2]							
		$V_{CC} = 0.8 \text{ V}$		-	23.2	-	-	-	-	-
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.4	6.0	13.1	2.2	14.8	16.3	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.0	4.2	7.6	1.8	9.0	9.9	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.7	3.6	6.1	1.5	7.2	8.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.4	2.9	4.8	1.3	5.7	6.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.2	2.5	4.3	1.1	5.1	5.7	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9

Symbol	Parameter	Conditions			25 °C		-40	°C to +1	25 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 pl$	F, 10 pF, 15 pF and	30 pF					•			
C _{PD}	power dissipation capacitance	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	<u>[3]</u>							
		$V_{CC} = 0.8 \text{ V}$		-	1.2	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	1.1	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	1.2	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	1.4	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	2.8	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	4.4	-	-	-	-	pF

- [1] All typical values are measured at nominal V_{CC}.
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}{}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}{}^2 \times f_o) \text{ where:}$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

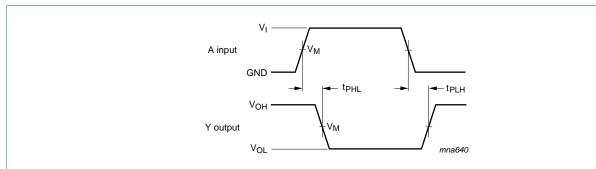
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



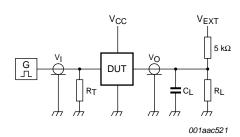
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 8. The data input (A) to output (Y) propagation delays

Table 9. Measurement points

Supply voltage	Output	Input					
V _{CC}	V _M	V _M	V _I	$t_r = t_f$			
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{CC}	≤ 3.0 ns			



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load	V _{EXT}			
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t_{PZL} , t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2\times V_{CC}$

[1] For measuring enable and disable times R_L = 5 $k\Omega$, for measuring propagation delays, setup and hold times and pulse width R_L = 1 $M\Omega$.

13. Additional characteristics

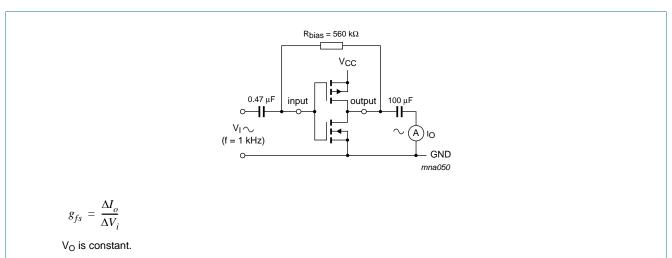
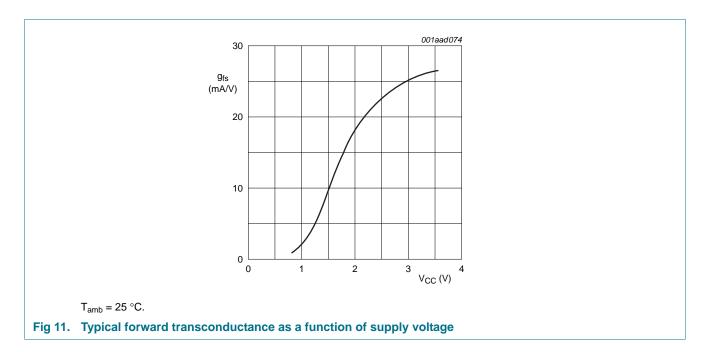


Fig 10. Test set-up for measuring forward transconductance

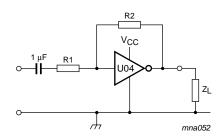


14. Application information

Some applications for the 74AUP1GU04 are:

- Linear amplifier (see Figure 12)
- Crystal oscillator (see Figure 13).

Remark: All values given are typical values unless otherwise specified.



 $Z_L > 10 \text{ k}\Omega$.

 $R1 \geq 3 \; k\Omega.$

 $R2 \leq 1~M\Omega.$

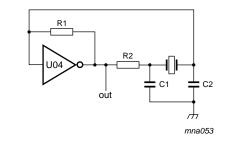
Open loop gain: $G_{OL} = 20$.

$$\mbox{Voltage amplification:} \ \, A_V = - \frac{G_{OL}}{I + \frac{RI}{R2}(I + G_{OL})} \, .$$

 $V_{o(p-p)} = V_{CC} - 1.5 \text{ V}$ centered at $0.5 \times V_{CC}$.

Unity gain bandwidth product is 5 MHz.

Fig 12. Linear amplifier application



C1 = 47 pF

C2 = 22 pF

R1 = 1 M Ω to 10 M Ω .

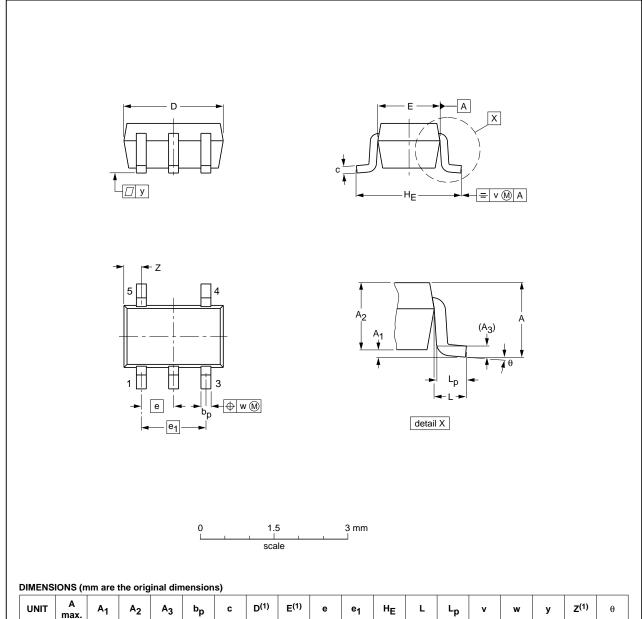
R2 optimum value depends on the frequency and required stability against changes in V_{CC} or average minimum I_{CC} (I_{CC} = 2 mA at V_{CC} = 3.3 V and f = 10 MHz).

Fig 13. Crystal oscillator application

15. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	C	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT353-1		MO-203	SC-88A			-00-09-01 03-02-19	

Fig 14. Package outline SOT353-1 (TSSOP5)

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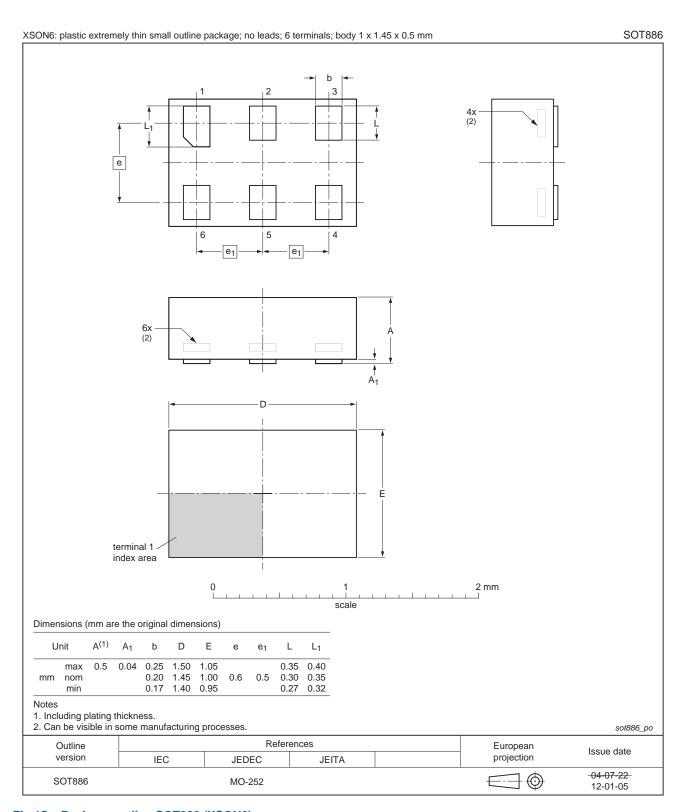


Fig 15. Package outline SOT886 (XSON6)

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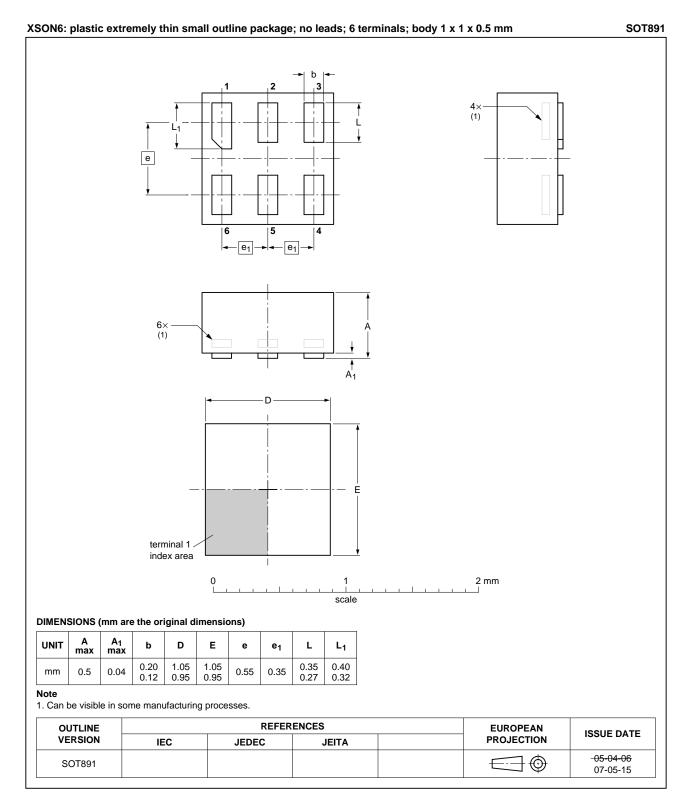


Fig 16. Package outline SOT891 (XSON6)

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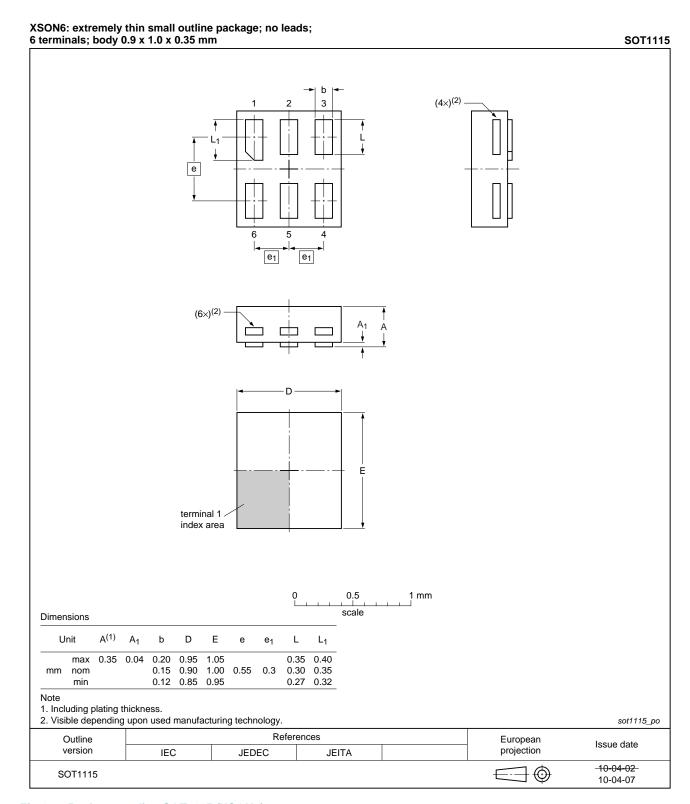


Fig 17. Package outline SOT1115 (XSON6)

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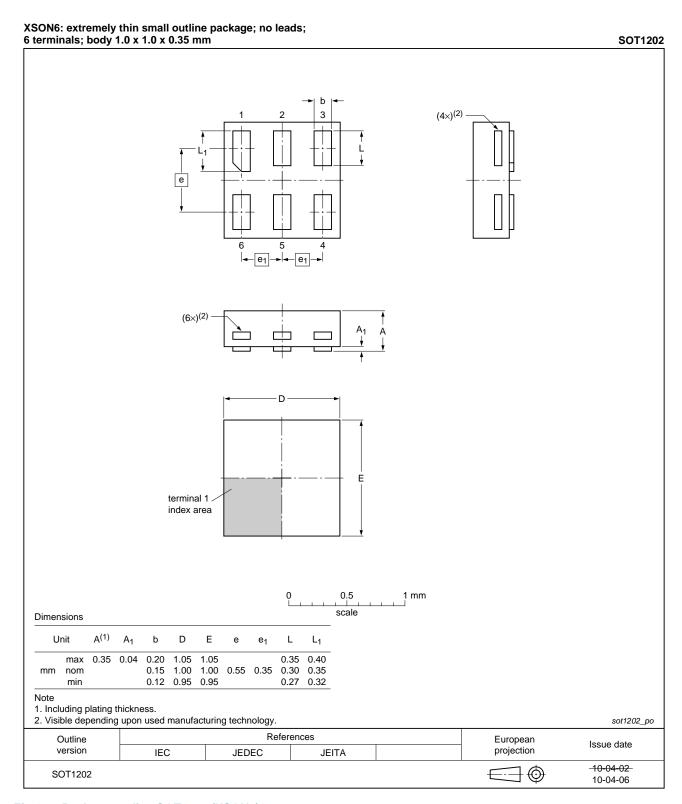


Fig 18. Package outline SOT1202 (XSON6)

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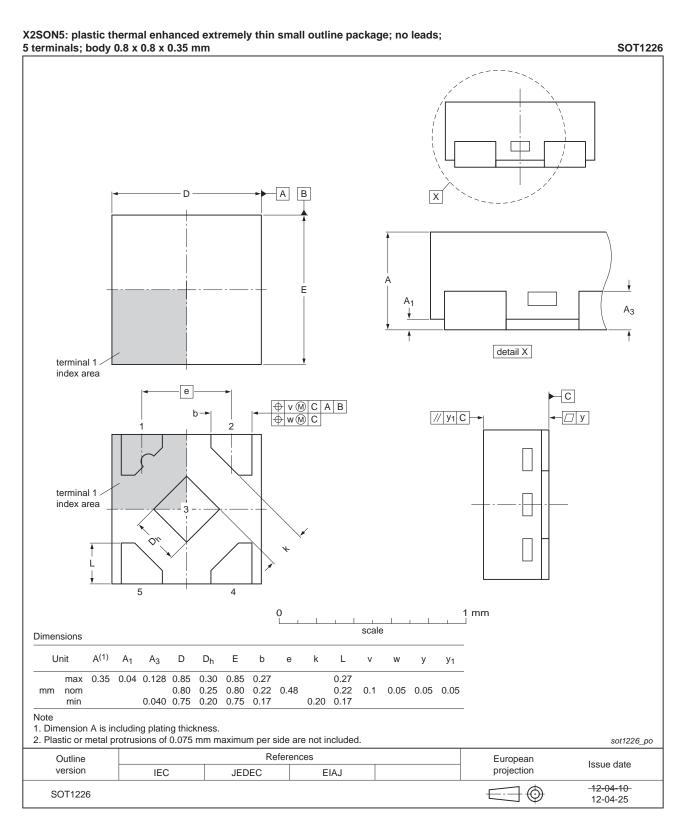


Fig 19. Package outline SOT1226 (X2SON5)

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16. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

17. Revision history

Table 12. Revision history

	_			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1GU04 v.5	20120629	Product data sheet	-	74AUP1GU04 v.4
Modifications:	 Added type i 	number 74AUP1GU04GX (S0)T1226)	
	 Package out 	line drawing of SOT886 (Figu	re 15) modified.	
74AUP1GU04 v.4	20111116	Product data sheet	-	74AUP1GU04 v.3
Modifications:	 Legal pages 	updated.		
	 Package out 	line drawing SOT363 replace	d by SOT353-1.	
74AUP1GU04 v.3	20100721	Product data sheet	-	74AUP1GU04 v.2
74AUP1GU04 v.2	20060803	Product data sheet	-	74AUP1GU04 v.1
74AUP1GU04 v.1	20050810	Product data sheet	-	-

18. Legal information

18.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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